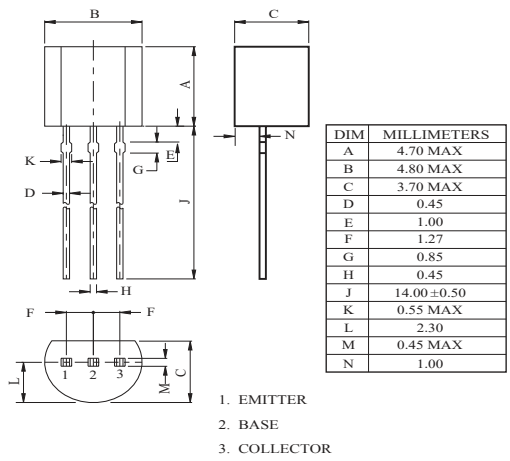
KTA733B

EPITAXIAL PLANAR PNP TRANSISTOR

GENERAL PURPOSE APPLICATION.
SWITCHING APPLICATION.

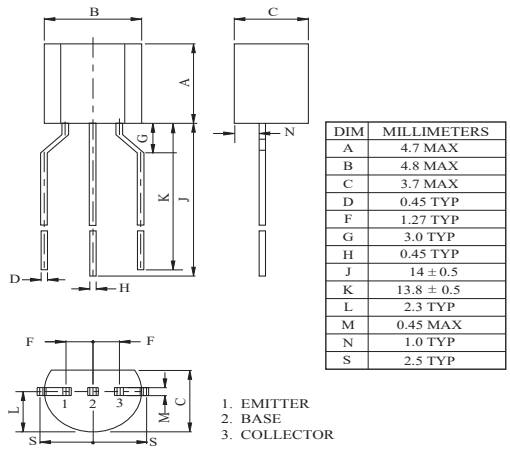
FEATURES

- Excellent h_{FE} Linearity.
  : $h_{FE}(I_C=0.1mA)/h_{FE}(I_C=2mA)=0.95$(Typ.)
- Low Noise : NF=1dB(Typ.). at f=1kHz
- Complementary to KTC945B.



DIM	MILLIMETERS
A	4.70 MAX
B	4.80 MAX
C	3.70 MAX
D	0.45
E	1.00
F	1.27
G	0.85
H	0.45
J	14.00±0.50
K	0.55 MAX
L	2.30
M	0.45 MAX
N	1.00

TO-92



DIM	MILLIMETERS
A	4.7 MAX
B	4.8 MAX
C	3.7 MAX
D	0.45 TYP
F	1.27 TYP
G	3.0 TYP
H	0.45 TYP
J	14 ± 0.5
K	13.8 ± 0.5
L	2.3 TYP
M	0.45 MAX
N	1.0 TYP
S	2.5 TYP

TO-92 AT TAPING TYPE

MAXIMUM RATING (Ta=25℃)

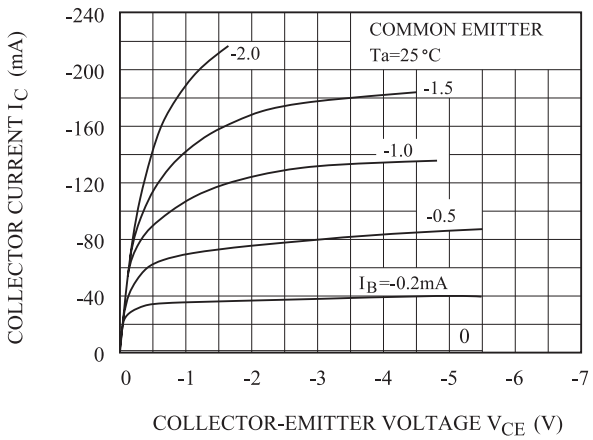
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-150	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 ~ 150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

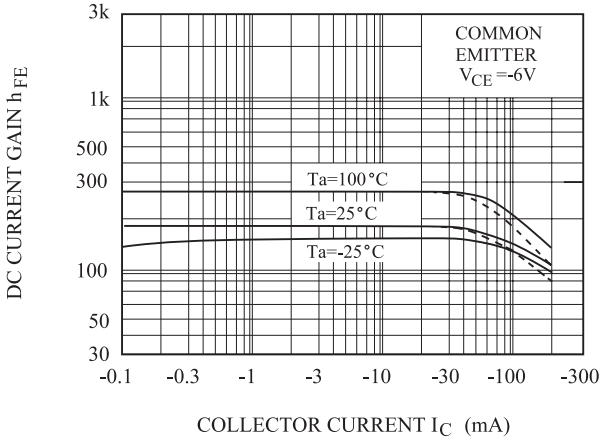
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=-100μA, I_E=0	-60	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-1mA, I_B=0	-50	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-100μA, I_C=0	-5	-	-	V
Collector Cut-off Current	I_{CBO}	V_{CB}=-50V, I_E=0	-	-	-0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-5V, I_C=0	-	-	-0.1	μA
DC Current Gain	h_{FE} (Note)	V_{CE}=-6V, I_C=-2mA	70	-	400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-100mA, I_B=-10mA	-	-0.1	-0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=-100mA, I_B=-10mA	-	-	-1.1	V
Transition Frequency	f_T	V_{CE}=-10V, I_C=-10mA	-	300	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	4	7	pF
Noise Figure	NF	V_{CE}=-6V, I_C=-0.1mA Rg=10kΩ, f=1kHz	-	1.0	10	dB

Note : h_{FE} Classification O:70 ~ 140, Y:120 ~ 240, GR:200 ~ 400

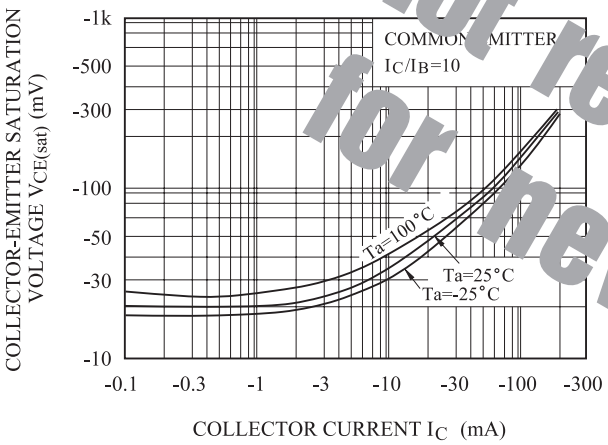
I_C - V_{CE}



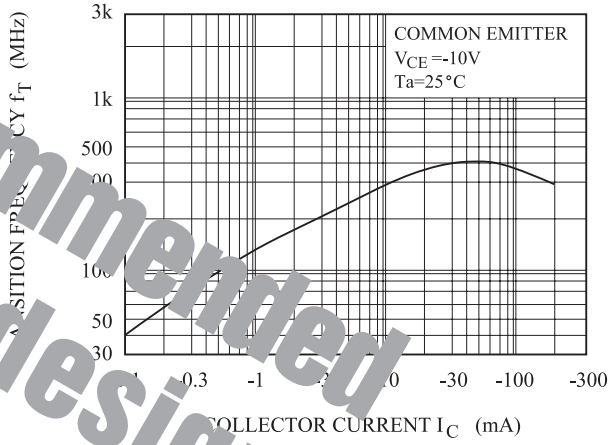
h_{FE} - I_C



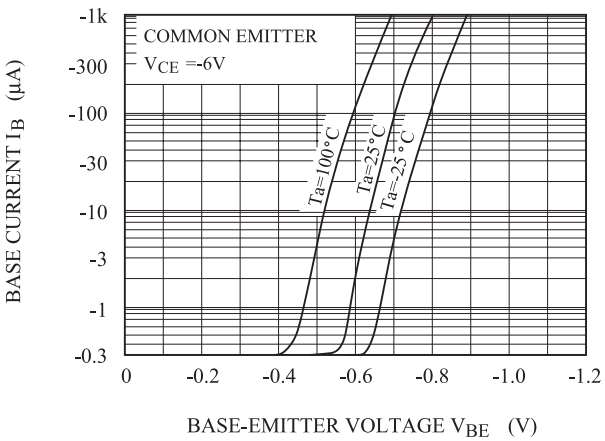
$V_{CE(sat)}$ - I_C



f_T - I_C



I_B - V_{BE}



Pc - Ta